

MMBD4448W SWITCHING DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

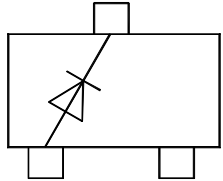
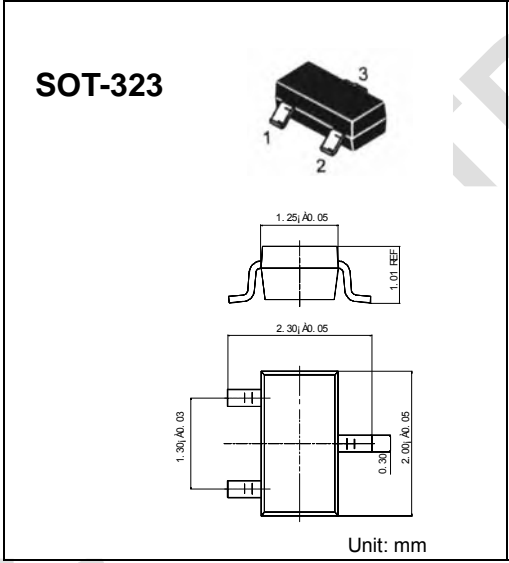
I_O : 250 mA

Collector-base voltage

V_R : 75 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



Marking: KA3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=10\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=20V$ $V_R=75V$		0.025 2.5	μA
Forward voltage	V_F	$I_F=5mA$ $I_F=10mA$ $I_F=100mA$ $I_F=150mA$		0.72 0.855 1 1.25	V
Diode capacitance	C_D	$V_R=0V, f=1MHz$		4	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	nS

Test period $<3000\mu s$.